

# **PATENT APPLICATION**

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Attn: OIPE

Izumi FUSEGAWA et al.

Application No.:

10/510,695

Docket No.:

121356

Filed: October 8, 2004

For:

METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON

SINGLE CRYSTAL AND SILICON WAFER

# REQUEST FOR CORRECTION OF PALM RECORDS

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

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Registration No. 30,024

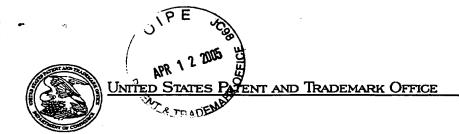
Philip A. Caramanica, Jr. Registration No. 51,528

WPB:PAC/nxy

Date: April 12, 2005

OLIFF & BERRIDGE, PLC P.O. Box 19928 Alexandria, Virginia 22320 Telephone: (703) 836-6400

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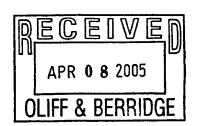
FILING OR 371 ART UNIT FIL FEE REC'D APPL NO. ATTY.DOCKET NO DRAWINGS TOT CLMS (c) DATE 10/510,695 10/08/2004 1765 950 121356 9

**CONFIRMATION NO. 3939** 

**FILING RECEIPT** 

Date Mailed: 04/05/2005

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### Applicant(s)

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#### **Assignment For Published Patent Application**

SHIN-ETSU HANDOTAI CO., LTD, Tokyo, JAPAN

Power of Attorney: The patent practitioners associated with Customer Number 25944.

# Domestic Priority data as claimed by applicant

This application is a 371 of PCT/JP03/05167 04/23/2003

#### Foreign Applications

JAPAN 2002-122250 04/24/2002

Projected Publication Date: 07/07/2005

Non-Publication Request: No

Early Publication Request: No

\* PLEASE SEE PAGE 2 FOR CORRECTIONS TO THETITLE \*

Title

-Method for producing silicon single crystal and, silicon single crystal and silicon wafer

METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL AND

Preliminary Class

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